

Silicon N Channel MOS FET Series Power Switching

> REJ03G1139-0400 Rev.4.00 Jul 13, 2007

Description

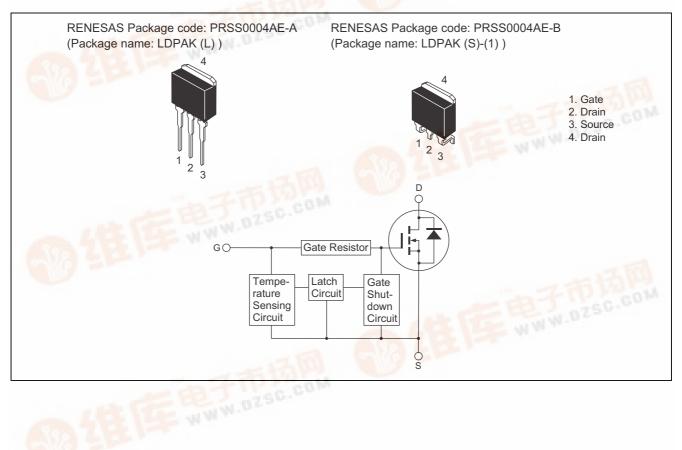
This FET has the over temperature shut-down capability sensing to the junction temperature.

This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

Features

- Logic level operation (4 to 6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Latch type shut-down operation (Need 0 voltage recovery)

Outline







Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	16	V
	V _{GSS}	-2.8	V
Drain current	ID	20	A
Drain peak current	I _{D (pulse)} Note 1	40	A
Body-drain diode reverse drain current	I _{DR}	20	A
Channel dissipation	Pch Note 2	50	W
Channel temperature	Tch	150	٥C
Storage temperature	Tstg	-55 to +150	٥C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Ta = 25°C

Typical Operation Characteristics

						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIH	3.5	—		V	
	VIL	_	—	1.2	V	
Input current	I _{IH1}	_	—	100	μΑ	$Vi = 8 V, V_{DS} = 0$
(Gate non shut down)	I _{IH2}	_	—	50	μΑ	Vi = 3.5 V, V _{DS} = 0
	IIL	_	—	1	μΑ	Vi = 1.2 V, V _{DS} = 0
Input current	I _{IH (sd) 1}	_	0.8		mA	$Vi = 8 V, V_{DS} = 0$
(Gate shut down)	I _{IH (sd) 2}	_	0.35		mA	Vi = 3.5 V, V _{DS} = 0
Shut down temperature	Tsd	_	175		°C	Channel temperature
Gate operation voltage	V _{OP}	3.5	_	13	V	

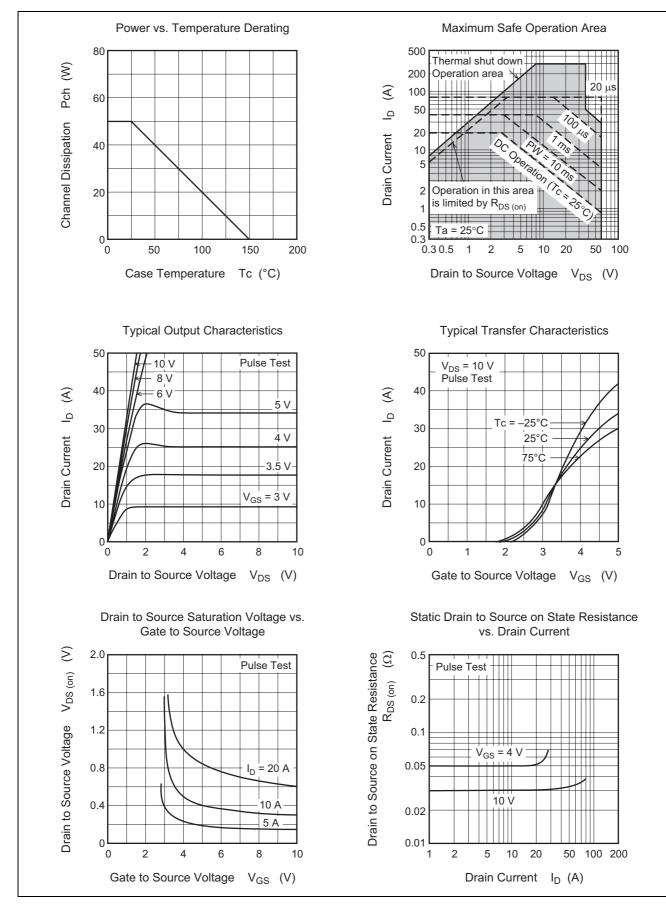
Electrical Characteristics

						(Ta = 25°C)
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current	I _{D1}	10			А	$V_{GS} = 3.5 \text{ V}, V_{DS} = 2 \text{ V}$
	I _{D2}			10	mA	$V_{GS} = 1.2 \text{ V}, V_{DS} = 2 \text{ V}$
Drain to source breakdown voltage	V (BR) DSS	60	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V (BR) GSS	16	—	_	V	$I_G = 100 \ \mu A, \ V_{DS} = 0$
	V (BR) GSS	-2.8	—	_	V	$I_G = -100 \ \mu A, V_{DS} = 0$
Gate to source leak current	I _{GSS1}		—	100	μΑ	$V_{GS} = 8 V, V_{DS} = 0$
	I _{GSS2}		—	50	μΑ	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
	I _{GSS3}		—	1	μΑ	$V_{GS} = 1.2 \text{ V}, V_{DS} = 0$
	I _{GSS4}		—	-100	μΑ	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	I _{GS (op) 1}		0.8	_	mA	$V_{GS} = 8 V, V_{DS} = 0$
	I _{GS (op) 2}		0.35	_	mA	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}		_	250	μΑ	$V_{DS} = 50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS (off)}	1.0	—	2.25	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R _{DS (on)}	_	50	65	mΩ	$I_D = 10 \text{ A}, V_{GS} = 4 \text{ V}^{Note 3}$
	R _{DS (on)}	_	30	43	mΩ	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{Note 3}$
Forward transfer admittance	y _{fs}	6	12	_	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{Note 3}$
Output capacitance	Coss		630	—	pF	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0$
						f = 1 MHz
Turn-on delay time	t _{d (on)}		7.5		μs	I _D = 5 A
Rise time	tr		29		μs	$V_{GS} = 5 V$
Turn-off delay time	t _{d (off)}		34		μs	$R_L = 6 \Omega$
Fall time	t _f		26		μs	
Body-drain diode forward voltage	V_{DF}		1.0		V	$I_F = 20 \text{ A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t _{rr}		110	_	ns	$I_F = 20 \text{ A}, V_{GS} = 0$
						di _F /dt = 50 A/µs
Over load shut down operation time Note4	t _{os1}	—	1.8	—	ms	V_{GS} = 5 V, V_{DD} = 12 V
	t _{os2}		0.7		ms	V_{GS} = 5 V, V_{DD} = 24 V

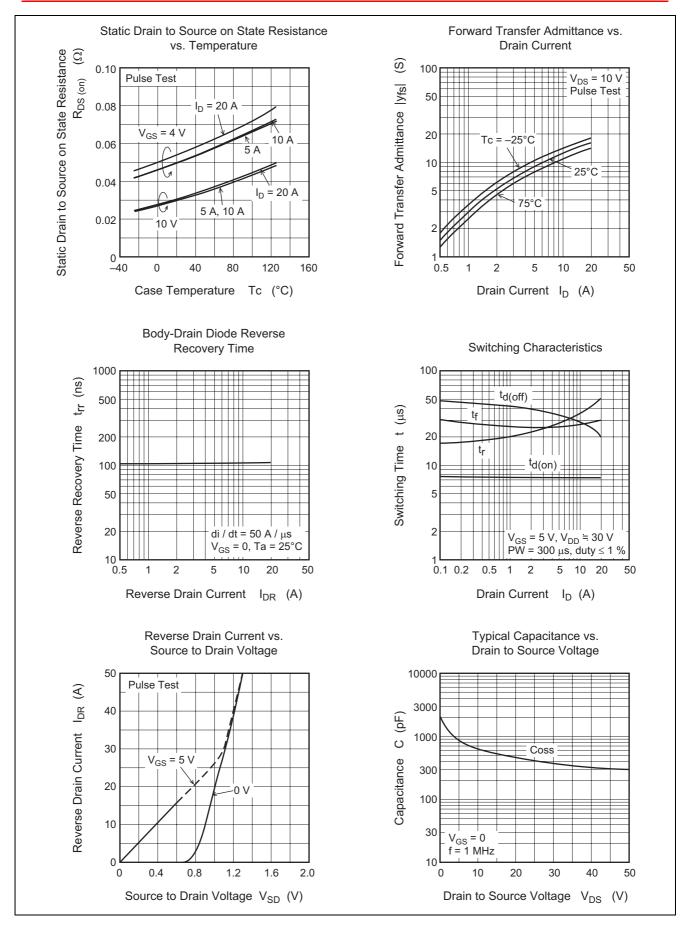
Notes: 3. Pulse test

4. Including the junction temperature rise of the over loaded condition.

Main Characteristics

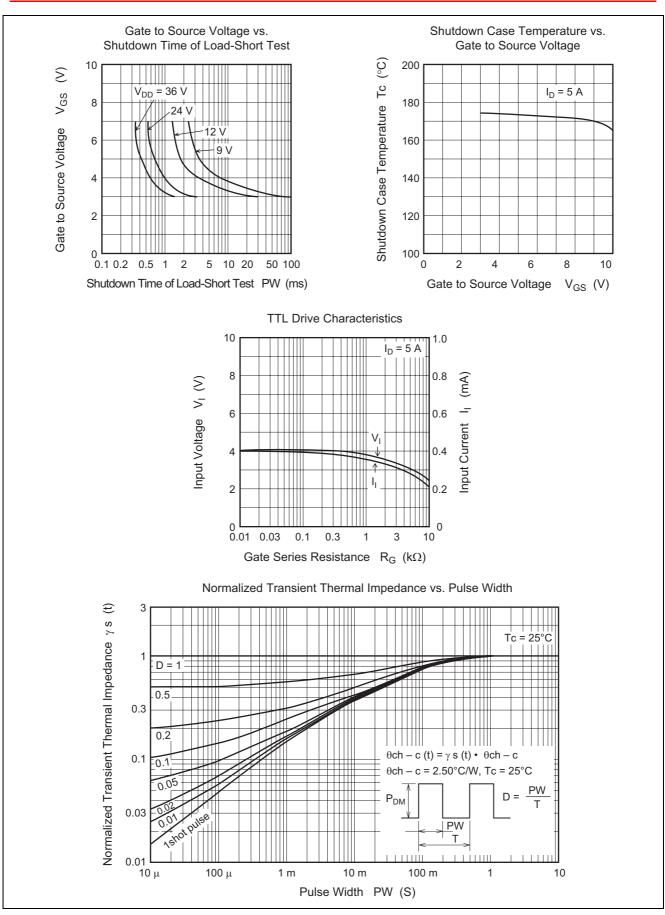


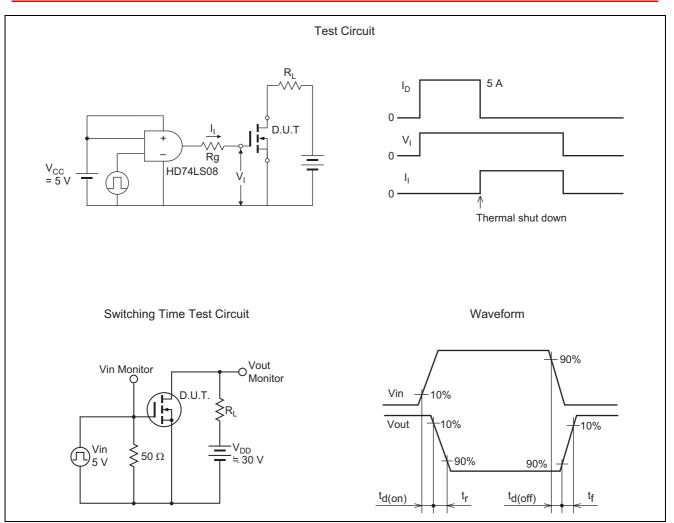
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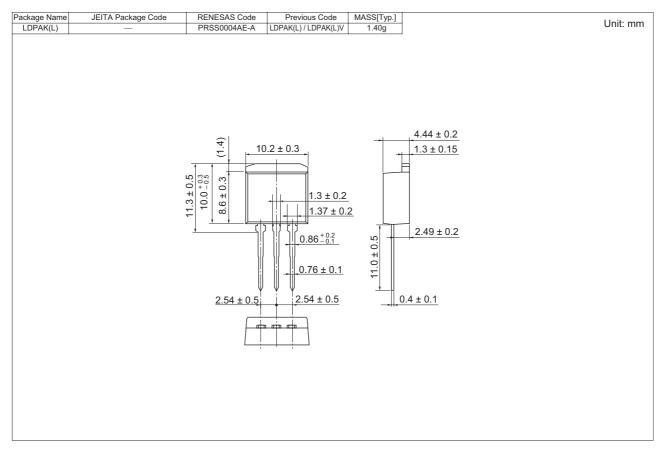
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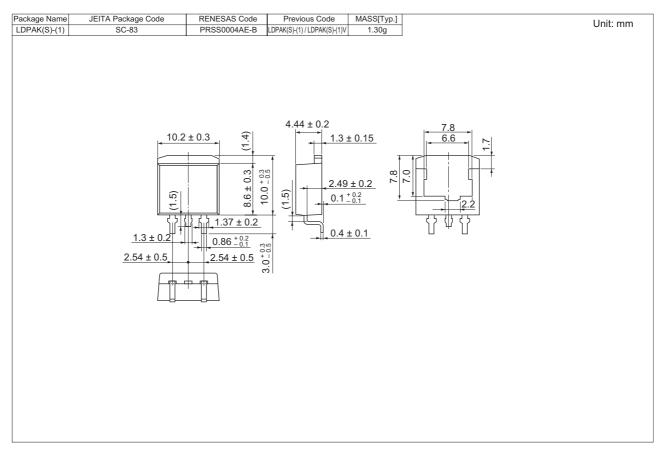
RENESAS





Package Dimensions





Ordering Information

Part Name	Quantity	Shipping Container
HAF2012-90L	Max: 50 pcs/sack	Sack
HAF2012-90S	Max: 50 pcs/sack	Sack
HAF2012-90STL	1000 pcs/Reel	Embossed tape
HAF2012-90STR	1000 pcs/Reel	Embossed tape

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